



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 150V
- I_D 115A
- $R_{DS(ON)}$



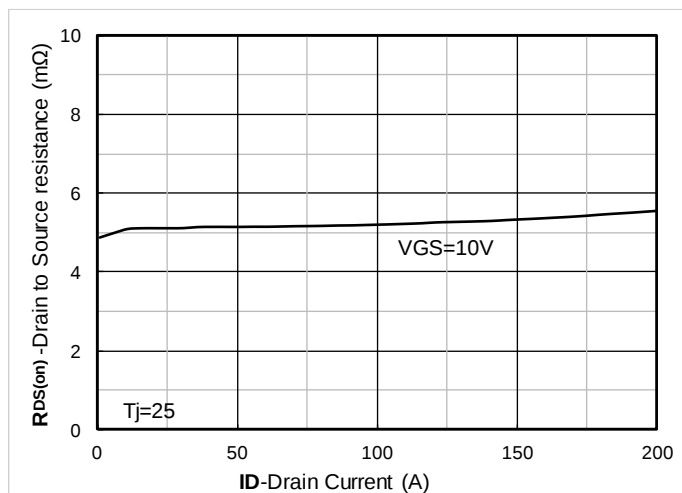


Figure 7. $R_{DS(on)}$ VS Drain Current

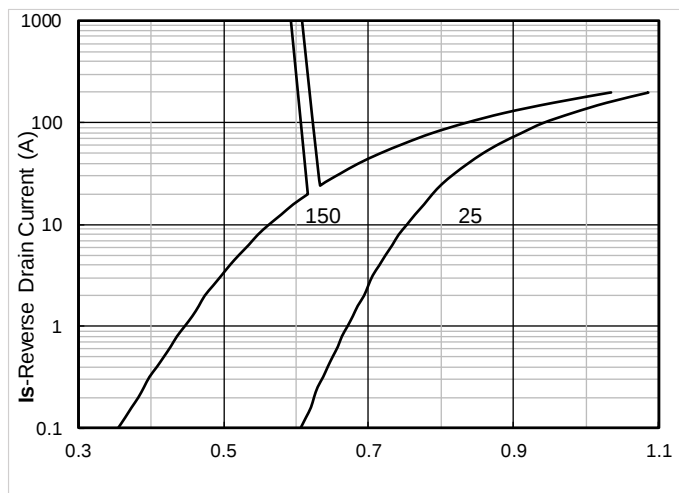


Figure 8. Forward characteristics of reverse diode

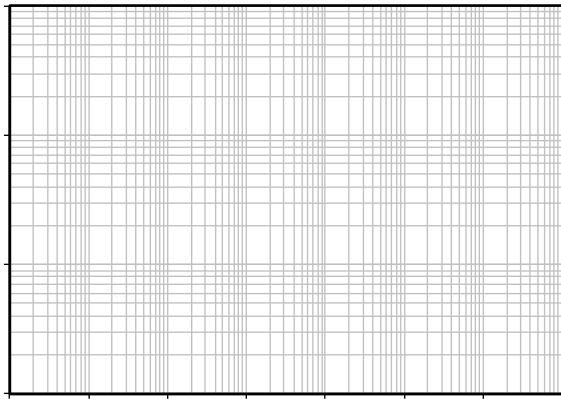


Figure 13. Maximum Transient Thermal Impedance

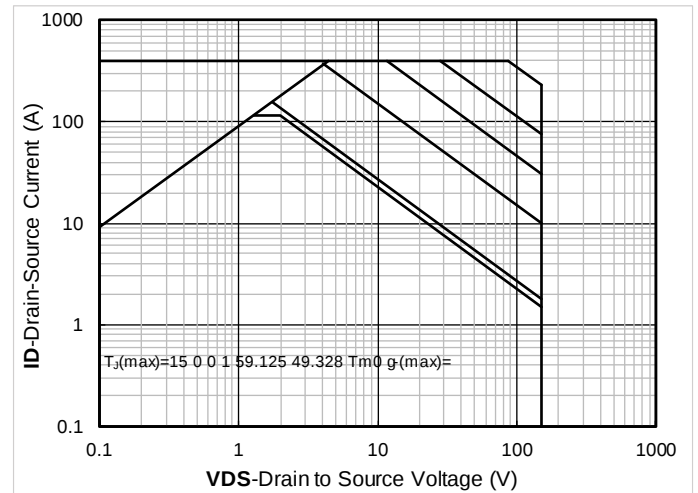


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

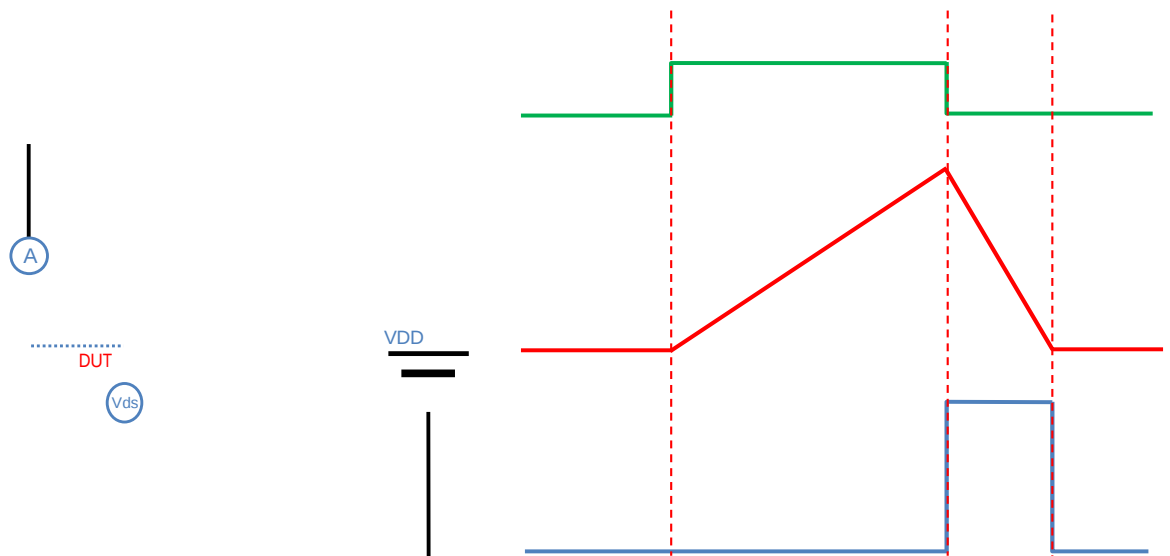


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

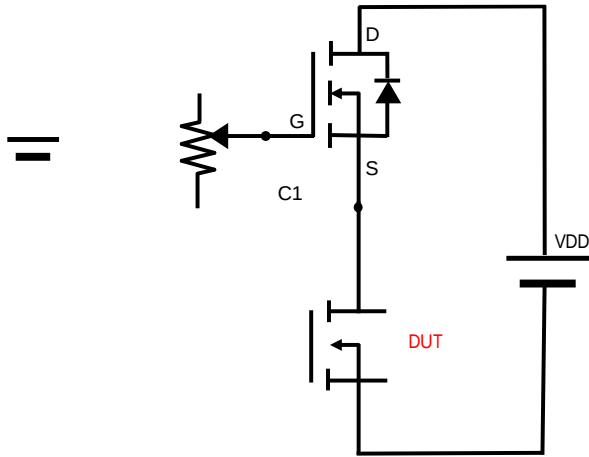


Figure B. Gate Charge Test Circuit & Waveform

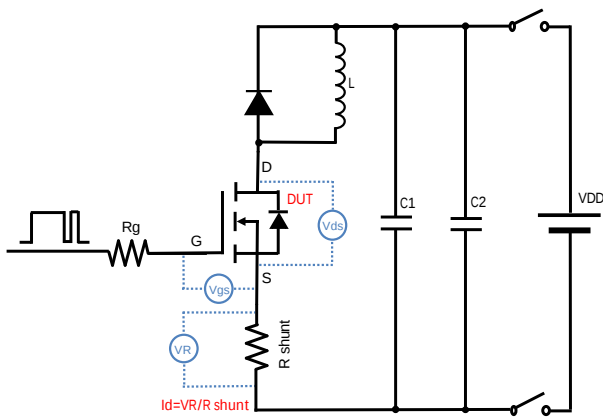


Figure C. Resistive Switching Test Circuit & Waveform

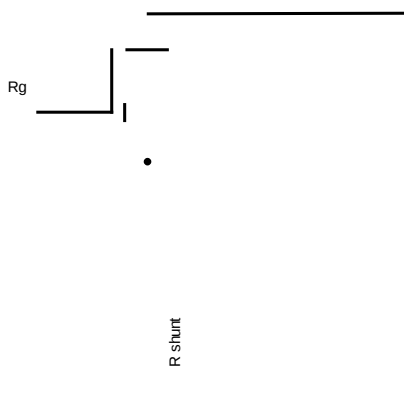


Figure D. Diode Recovery Test Circuit & Waveform



■ TO-263-HY Package information

SYM.	MIN.	
A2		
b2		0.050
c		
c2		
D2		
E		
E1		



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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with